

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re the Application of:

HYUN-SOO KIM, ET AL.

Application No.:

Filed:

For: **High Speed Optical Signal Processor  
Including Saturable Absorber and  
Gain-Clamped Optical Amplifier**

Art Group:

Examiner:

**INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure, enclosed is a copy of Information Disclosure Statement by Applicant (form PTO/SB/08), which is being submitted concurrently with the Utility Application. It is respectfully requested that the cited references be considered and that the enclosed copy of PTO/SB/08 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

The submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made in the subject application and is not to be construed as an admission that the information cited in this statement is material to patentability.

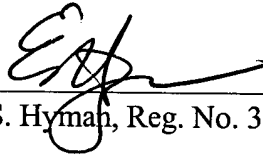
Please charge any fees due to Deposit Account 02-2666. A duplicate copy of the Fee Transmittal (PTO/SB/17) is enclosed for this purpose.

Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP

Date: \_\_\_\_\_

9/2/03



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## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

**Complete if Known**

Filing Date

**First Named Inventor**

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Hyun-Soo Kim

**Art Unit**

Examiner Name

Attorney Docket Number

3364P139

Sheet

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Examiner  
Initials\*Cite  
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Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.

 $T^2$ 

IEEE Journal, Vol. 7, No. 2, March/April 2001, "Fabrication of Saturable Absorbers in InGaAsP-InP Bulk Semiconductor Laser Diodes by Heavy Ion Implantation, M. Dulk, et al.

Cleo '97, Tuesday, May 20, pages 124 and 125

**Examiner  
Signature**

Date Considered
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\*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication.

<sup>1</sup>Applicant's unique citation designation number. <sup>2</sup>Applicant is to place a check mark here if English language Translation is attached.

Based on PTO/SB/08B (08-03) as modified by Blakely, Solokoff, Taylor & Zafman (wlr) 08/11/2003.  
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